SMT720

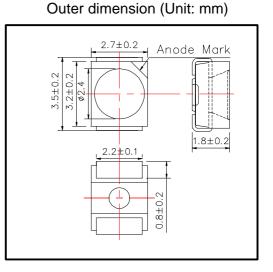
High Performance Infrared TOP IR LED

SMT720 consists of an AlGaAs LED mounted on the lead frame as TOP LED package and is 10 mW typical of output power.

It emits a spectral band of radiation at 720 nm.

Specifications

1) Product Name 2) Type No.	TOP IR LED SMT720
 Chip Chip Material 	AlGaAs
(2) Peak Wavelength4) Package	720 nm typ.
(1) Lead Frame Die(2) Package Resin(3) Lens	Silver Plated PPA Resin Epoxy Resin



Absolute Maximum Rating

Item	Symbol	Maximum Rated Value Unit		Ambient Temperature	
Power Dissipation	Po	100	mW	Ta = 25°C	
Forward Current	lf	50	mA	Ta = 25°C	
Pulse Forward Current	IFP	200	mA	Ta = 25°C	
Reverse Voltage	Vr	5	V	Ta = 25°C	
Operating Temperature	Topr	-20 ~ +80	°C		
Storage Temperature	Tstg	-30 ~ +80	°C		
Soldering Temperature	Tsol	240	°C		

 \pm Pulse Forward Current condition: Duty = 1% and Pulse Width = 10 μ s. \pm Soldering condition: Soldering condition must be completed within 3 seconds at 260°C

Electro-Optical Characteristics [Ta=25°C]

Item	Symbol	Condition	Minimum	Typical	Maximum	Unit
Forward Voltage	VF	l⊧=50mA		1.90	2.30	V
Reverse Current	IR	Vr=5V			10	uA
Total Radiated Power	Po	l⊧=50mA	5.0	10.0		mW
Radiant Intensity	ΙE	l⊧=50mA	2.0	5.0		mW/sr
Peak Wavelength	I P	l⊧=50mA		720		nm
Half Width	DI	l⊧=50mA		20		nm
Viewing Half Angle	Q 1/2	l⊧=50mA		±55		deg.
Rise Time	tr	I⊧=50mA		80		ns
Fall Time	tf	I⊧=50mA		80		ns

‡Total Radiated Power is measured by Photodyne #500

‡Radiant Intensity is measured by Tektronix J-6512.